

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L20	1	( semiconductor adj2 insulator and substrate and top adj semiconductor adj layer and crystalline adj structure and first adj type and second adj type and characterized and strained). clm.	US-PGPU B	OR	ON	2005/11/01 15:09

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1142	("SiGe" 'sige' silicon near3 geranium) with (strained relaxed)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:53
L2	849	L1 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation oxynitridation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:53
L3	231	L2 and ("SiGe" 'sige' silicon near3 geranium) with (crystalline ((mono single) near3 (crystal crystalline)))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:53
L4	215	L3 and ("SiGe" 'sige' silicon near3 geranium) with ('soi' insulat\$3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:53
L5	215	L3 and ("SiGe" 'sige' silicon near3 geranium) with ('soi' insulat\$3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:54
L6	215	L5 and (nitride silicon oxynitride nitrogen germanium metal metal\$4 heat\$3 anneal\$3 oxide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:54
L7	123	L6 and \$4nitrid\$7	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:54
L8	1500	("SOI" semiconductor adj on adj insulator) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:55
L9	434	L8 and (crystal\$5) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:55
L10	182	L9 and (implant\$4 nitridation nitrify nitrification silicide silicidation oxynitridation oxidation) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:55

L11	125	L10 and (strained) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:55
L12	25	L11 and (nitride) with (silicon adj germanium 'sige')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/01 14:55